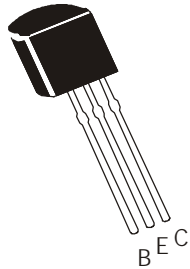


NPN SILICON PLANAR EPITAXIAL TRANSISTOR

MPSH10



TO-92
Plastic Package

VHF/UHF Transistor

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$ unless specified otherwise)

DESCRIPTION	SYMBOL	VALUE	UNITS
Collector Emitter Voltage	V_{CEO}	25	V
Collector Base Voltage	V_{CBO}	30	V
Emitter Base Voltage	V_{EBO}	3.0	V
Power Dissipation @ $T_a=25^\circ\text{C}$	P_D	350	mW
Derate Above 25°C		2.8	mW/ $^\circ\text{C}$
Power Dissipation @ $T_c=25^\circ\text{C}$	P_D	1.0	W
Derate Above 25°C		8.0	mW/ $^\circ\text{C}$
Operating And Storage Junction Temperature Range	T_j, T_{stg}	- 55 to +150	$^\circ\text{C}$

THERMAL RESISTANCE

Junction to Ambient in free air	$R_{th(j-a)}$	357	$^\circ\text{C/W}$
Junction to case	$R_{th(j-c)}$	125	$^\circ\text{C/W}$

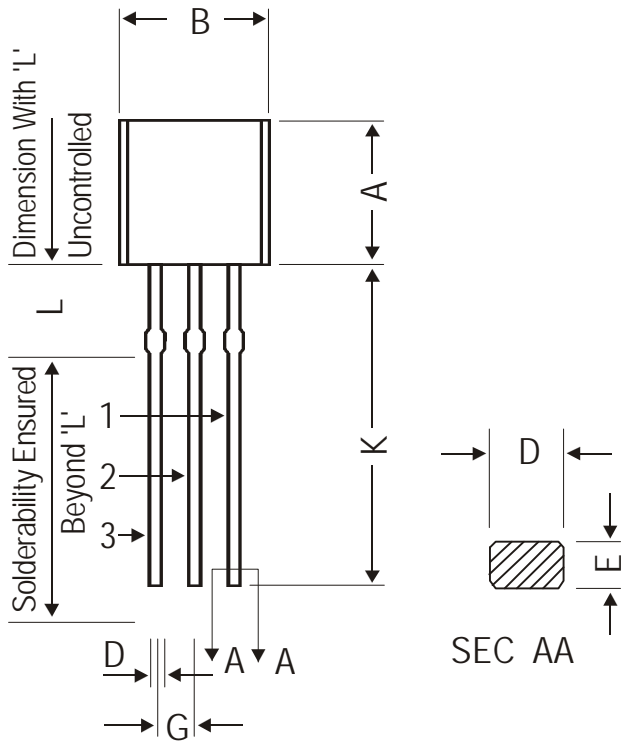
ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$ unless specified otherwise)

DESCRIPTION	SYMBOL	TEST CONDITION	MIN	MAX	UNITS
Collector Emitter Voltage	V_{CEO}	$I_C=1\text{mA}, I_B=0$	25		V
Collector Base Voltage	V_{CBO}	$I_C=100\mu\text{A}, I_E=0$	30		V
Emitter Base Voltage	V_{EBO}	$I_E=10\mu\text{A}, I_C=0$	3.0		V
Collector Cut Off Current	I_{CBO}	$V_{CB}=25\text{V}, I_E=0$		100	nA
Emitter Cut Off Current	I_{EBO}	$V_{EB}=2\text{V}, I_C=0$		100	nA
DC Current Gain	h_{FE}	$I_C=4\text{mA}, V_{CE}=10\text{V}$	60		
Collector Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=4\text{mA}, I_B=0.4\text{mA}$		0.50	V
Base Emitter On Voltage	$V_{BE(on)}$	$I_C=4\text{mA}, V_{CE}=10\text{V}$		0.95	V

DYNAMIC CHARACTERISTICS

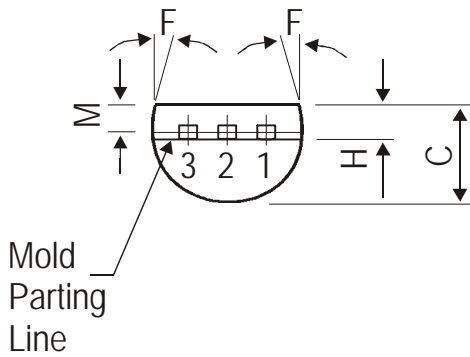
DESCRIPTION	SYMBOL	TEST CONDITION	MIN	MAX	UNITS
Transition Frequency	f_T	$I_C=4\text{mA}, V_{CE}=10\text{V}, f=100\text{MHz}$	650		MHz
Collector Base Capacitance	C_{cb}	$V_{CB}=10\text{V}, I_E=0, f=1\text{MHz}$		0.70	pF
Common Base feedback Capacitance	C_{fb}	$V_{CB}=10\text{V}, I_E=0, f=1\text{MHz}$	0.35	0.65	pF
Collector Base Time Constant	$rb' C_C$	$I_C=4\text{mA}, V_{CB}=10\text{V}, f=31.8\text{MHz}$		9.00	ps

TO-92 Plastic Package



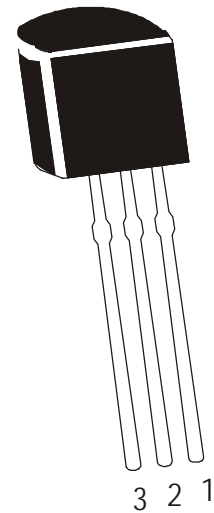
DIM	MIN.	MAX.
A	4.32	5.33
B	4.45	5.20
C	3.18	4.19
D	0.41	0.55
E	0.35	0.50
F	5 DEG	
G	1.14	1.40
H	1.20	1.40
K	12.70	—
L	1.982	2.082
M	1.03	1.20

All dimensions are in mm



PIN CONFIGURATION

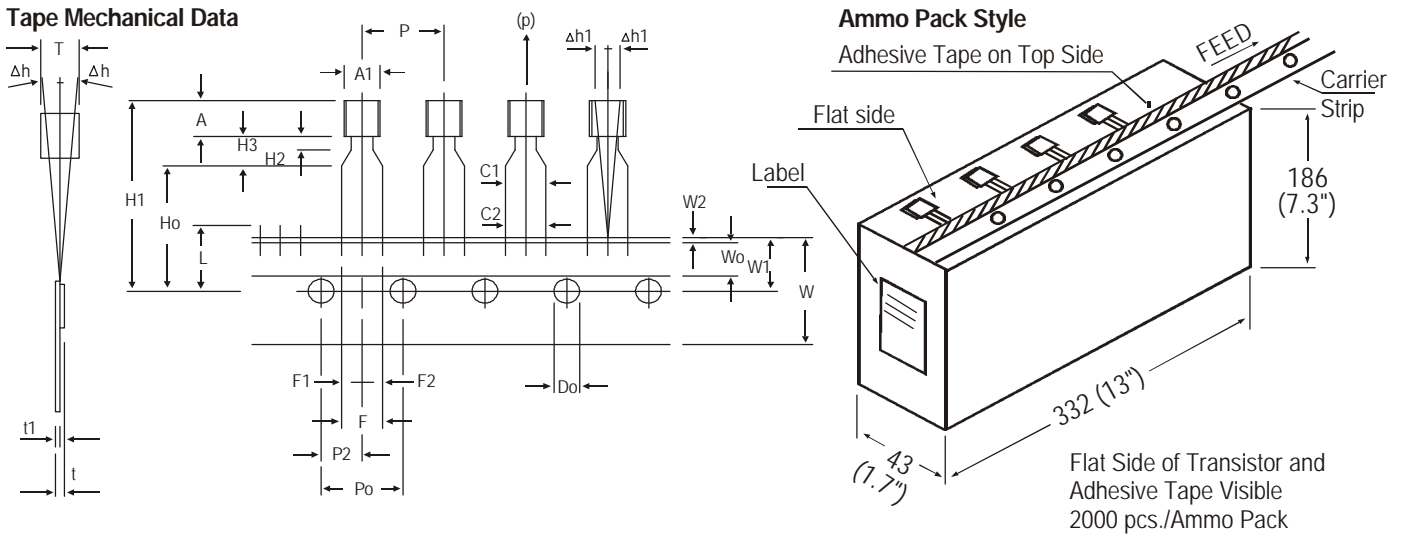
1. COLLECTOR
2. EMITTER
3. BASE



Packing Details

PACKAGE	STANDARD PACK		INNER CARTON BOX		OUTER CARTON BOX		
	Details	Net Weight/Qty	Size	Qty	Size	Qty	Gr Wt
TO-92 Bulk	1K/polybag	200 gm/1K pcs	3" x 7.5" x 7.5"	5K	17" x 15" x 13.5"	80K	23 kgs
TO-92 T&A	2K/ammo box	645 gm/2K pcs	12.5" x 8" x 1.8"	2K	17" x 15" x 13.5"	32K	12.5 kgs

TO-92 Tape and Ammo Pack



All dimensions are in mm

ITEM	SYMBOL	SPECIFICATION			
		MIN.	NOM.	MAX.	TOL.
BODY WIDTH	A1	4.0		4.8	
BODY HEIGHT	A	4.8		5.2	
BODY THICKNESS	T	3.9		4.2	
PITCH OF COMPONENT	P		12.7		± 1.0
*1 FEED HOLE PITCH	Po		12.7		± 0.3
*2 FEED HOLE CENTRE TO COMPONENT CENTRE	P2		6.35		± 0.4
DISTANCE BETWEEN OUTER LEADS	F		5.08		+ 0.6 - 0.2
*3 COMPONENT ALIGNMENT SIDE VIEW	Δh		0	1.0	
*4 COMPONENT ALIGNMENT FRONT VIEW	Δh1		0	1.3	
TAPE WIDTH	W		18		± 0.5
HOLD-DOWN TAPE WIDTH	Wo		6		± 0.2
HOLE POSITION	W1		9		+ 0.7 - 0.5
HOLD-DOWN TAPE POSITION	W2		0.5		± 0.2
LEAD WIRE CLINCH HEIGHT	Ho		16		± 0.5
COMPONENT HEIGHT	H1			23.25	
LENGTH OF SNIPPED LEADS	L			11.0	
FEED HOLE DIAMETER	Do		4		± 0.2
*5 TOTAL TAPE THICKNESS	t			1.2	
LEAD - TO - LEAD DISTANCE	F1, F2		2.54		+ 0.4 - 0.1
STAND OFF	H2	0.45		1.45	
CLINCH HEIGHT	H3			3.0	
LEAD PARALLELISM	C1 - C2			0.22	
PULL - OUT FORCE	(p)	6N			

NOTES

1. Maximum alignment deviation between leads will not to be greater than 0.2mm.
2. Maximum non-cumulative variation between tape feed holes shall not exceed 1 mm in 20 pitches.
3. Holddown tape will not exceed beyond the edge(s) of carrier tape and there shall be no exposure of adhesive.
4. There will be no more than three (3) consecutive missing components in a tape.
5. A tape trailer, having at least three feed holes are provided after the last component in a tape.
6. Splices should not interfere with the sprocket feed holes.

REMARKS

- *1 Cumulative pitch error 1.0 mm/20 pitch
- *2 To be measured at bottom of clinch
- *3 At top of body
- *4 At top of body
- *5 t1 0.3 – 0.6 mm

Disclaimer

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